TOSHIBA TC90A13N/F

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

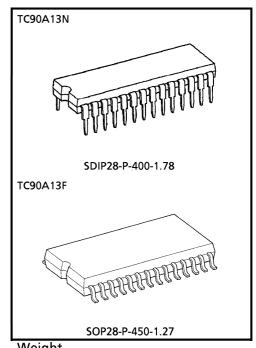
# TC90A13N, TC90A13F

# 3 LINE DIGITAL Y/C SEPARATION IC

The TC90A13N and TC90A13F separate luminance (Y) and chrominance (C) signals from an NTSC composite video signal. It employs the Toshiba original logical comb filter to realize high performance Y/C separation at low cost.

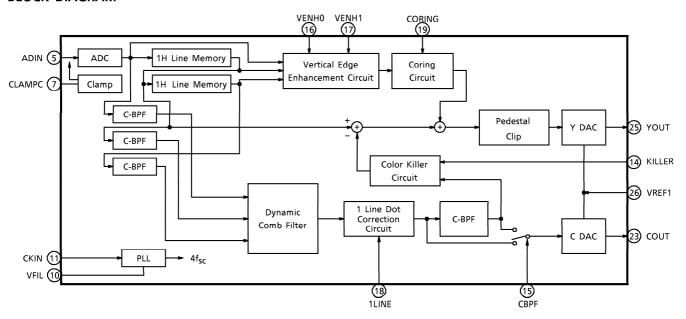
## **FEATURES**

- NTSC system
- PLL 4X multiplication circuit
- Sync. tip clampping circuit
- 8bit A/D converter
- 8bit D/A converters (2ch)
- 2H line memory
- Dynamic comb filter
- 1 line dot correction circuit
- Vertical enhancer
- Color killer mode (Y/C separation OFF)
- Chrominance wide band output mode
- SDIP28/SOP28 package
- 5V single power supply

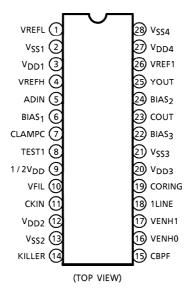


Weight SDIP28-P-400-1.78 : 1.7g (Typ.) SOP28-P-450-1.27 : 0.8g (Typ.)

## **BLOCK DIAGRAM**



## **TERMINAL CONNECTION DIAGRAM**



# **TERMINAL FUNCTION**

PIN No.	NAME	FUNCTION	PIN No.	NAME	FUNCTION
1	VREFL	Bias for ADC	15	CBPF	L : C-BPF = WIDE, H : NARROW
2	V <sub>SS1</sub>	GND for ADC	16	VENH0	Vertical edge enhanced level (VENH0, VENH1) = (L, L) = OFF
3	V <sub>DD1</sub>	V <sub>DD</sub> for ADC	17	VENH1	(H, L) = Low (L, H) = MID, (H, H) = High
4	VREFH	Bias for ADC	18	1LINE	L : 1 line color ON H : 1 line color OFF
5	ADIN	Video input	19	CORING	L : Coring ON H : Coring OFF
6	BIAS <sub>1</sub>	Bias for ADC	20	$V_{DD3}$	V <sub>DD</sub> for digital
7	CLAMPC	Clamp filter	21	V <sub>SS3</sub>	GND for digital
8	TEST1	Test terminal	22	BIAS <sub>3</sub>	Bias for DAC
9	1/2V <sub>DD</sub>	Bias for line memory	23	COUT	C output
10	VFIL	VCO filter	24	BIAS <sub>2</sub>	Bias for DAC
11	CKIN	Clock input	25	YOUT	Y output
12	$V_{DD2}$	V <sub>DD</sub> for PLL	26	VREF1	Bias for DAC
13	$V_{SS2}$	GND for PLL	27	$V_{DD4}$	V <sub>DD</sub> for DAC
14	KILLER	L:Color, H:B/W mode	28	V <sub>SS4</sub>	GND for DAC

(Note) Pin 9 and Pin 26 require external bias

#### **FUNCTION BLOCK DESCRIPTIONS**

## 1. Input clamp (CLAMP)

This block performs sync tip clamping of the composite video signal. It provides a feedback signal for clamping A/D-converted minimum data at Y/C separation to the internal DC bias level.

#### 2. A/D converter (ADC)

This block comprises a high-speed series-parallel 8bit A/D converter that accepts an input video signal of  $1.5V_{D-D}$  (from sync level to 100% white level).

## 3. 1H memory

This block consists of DRAM resident line memory for 1H delay. The 3-line comb filter is configured from two pairs of line memory.

# 4. Vertical edge enhancement circuit (VENH)

This block enhances the uncorrelated components among the three lines of the luminance signal following coring. There are three enhancement level selections of HIGH (1.9dB), MID (1.0dB) and LOW 0.5dB). The luminance signal, obtained by subtracting the chrominance signal from the composite video signal, is added to the vertical edge enhancement component and output through the D/A converter. However, this output signal is limited to the pedestal level (fixed internally) by the pedestal clipping circuit (except for the sync tip level).

## 5. Horizontal band-pass filter (BPF)

In this block, with fsc as the center frequency of the BPF, the chrominance signal is extracted from the 0H, 1H and 2H delayed composite video signal. Since the BPF for the chrominance signal output can be controlled (ON or OFF), the chrominance output can therefore be switched between a narrow band width and a wide band width.

## 6. Vertical dynamic comb filter (DCF)

This block comprises a band-pass filter that extracts the vertical component of the chrominance signal. Using Toshiba original logic, a correlation of the three lines is sought for. The absence of correlation is taken as an indication of a luminance signal, at which time chrominance signal output is suppressed.

### 7. 1-line dot correction circuit

Previously, a 1-line-only chrominance signal was processed as a luminance signal resulting in dot crawl. This circuit prevents this problem by extracting the 1-line dot component and adding it to the dynamic comb filter output. This circuit block can be set ON or OFF.

## 8. Clock and memory timing generator (RTIM)

This block supplies a 4 fsc (PLL 4X multiplied) buffered signal to the other circuit blocks, and also generates a timing signal for the memory.

#### 9. D/A converter (DAC)

This block comprises a high-speed 8bit D/A converter. It provides Y output at approximately  $1.5V_{p-p}$  and burst-level C output at approximately  $572mV_{p-p}$ .

# **MODE TABLE**

PIN 14 KILLER	PIN 15 CBPF	PIN 16 VENH0	PIN 17 VENH1	PIN 18 1 LINE	PIN 19 CORING	MODE	ACTION
L	_	_	_	_	_	Y/C separation ON	Color mode
Н				_	_	Y/C separation OFF	B/W mode (Killer)
_	L	1	ı	1	_	Chrominance signal horizontal band width WIDE	Passes through BPF for chrominance signal output
	I	1	1			Chrominance signal horizontal band width NARROW	Does not pass through BPF for chrominance signal output
_	_	L	L	_	_	Vertical enhance OFF	No vertical enhancement
_		Н	L	_	_	Vertical enhance level MID	Vertical enhancement level 0.5dB
_		L	Н	_	_	Vertical enhance level LOW	Vertical enhancement level 1.0dB
		Н	Н	_	_	Vertical enhance level HIGH	Vertical enhancement level 1.9dB
_		_		L	_	1 line color ON	1 line dot correction circuit ON
_		_		Н	_	1 line color OFF	1 line dot correction circuit OFF
_	_	_	_		L	Coring ON	Coring circuit ON
_			_		Н	Coring OFF	Coring circuit OFF

# **RATINGS AND CHARACTERISTICS**

The following specifications were obtained in part from the test circuit shown on page 8.

# **MAXIMUM RATINGS** (Ta = $25^{\circ}$ C)

CHARACTER	CHARACTERISTIC		CHARACTERISTIC		RATING	UNIT
Power Supply Volt	age	$V_{DD}$	V55~V55 + 6.0	V		
Input Voltage		$v_{IN}$	-0.3~V <sub>DD</sub> +0.3	٧		
Power Dissipation	TC90A13N	P <sub>D</sub> (Note)	900	mW		
l ower bissipation	TC90A13F	TD (Note)	600	11100		
Storage Temperatu	ire	T <sub>stg</sub>	<b>-</b> 55∼125	°C		

(Note)  $Ta = 75^{\circ}C$ 

# **RECOMMENDED OPERATING CONDITIONS**

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Power Supply Voltage	$V_{DD}$	_	4.75	5.0	5.25	V
Input Voltage	VIN	_	0	_	$V_{DD}$	V
Operating Temperature	T <sub>opr</sub>	1	- 10		75	°C

# **ELECTRICAL CHARACTERISTICS**

DC CHARACTERISTICS (Ta = 25°C,  $V_{DD} = 5V$ )

CHARACT	ERISTIC	SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Power Supply \	/oltage	$V_{DD}$	1		4.75	5.0	5.25	<b>V</b>
Supply Current		$I_{DD}$	1		40	60	80	mΑ
Output Voltage Level		Yout	1		3.0	3.15	3.3	v
		COUT	'		3.9	4.0	4.1	V
		VREFL			1.4	1.5	1.6	
		VREFH		$CLOCK = 3.579545MHz$ $500mV_{p-p}$ $VREF1 = 3.0V$ $1/2V_{DD} = 2.5V$ $V_{IN} = No input (Note 2)$	3.4	3.5	3.6	V
		ADIN			1.5	1.6	1.8	
		BIAS <sub>1</sub>			0.8	1.4	2.4	
Pin Voltage Lev	/el	BIAS <sub>2</sub>	1		0.8	1.6	2.6	
		BIAS <sub>3</sub>			2.4	3.4	4.4	
		CLAMPC	1		2.0	3.0	4.0	
		VFIL			0.9	1.9	2.9	
					1.5	2.2	3.0	
Input Voltage	High Level	V <sub>IH</sub>	1		4	_	_	.,
input voitage	Low Level	V <sub>IL</sub>	1		_	_	1	V
ADIN Pin Input Capacitance		CIN	1		_	50	_	рF
Pull Down Resi	stance	R <sub>PD</sub>	1		25	50	100	kΩ

(Note 1) External bias must be applied at Pin 9 and Pin 26.

(Note 2)  $I_{DD}$  is  $V_{IN} = modulated lamp wave.$ 

AC CHARACTERISTICS Y output ( $Ta = 25^{\circ}C$ ,  $V_{DD} = 5V$ , Clock frequency 3.579545MHz, 0.5Vp-p, S1 = 2,  $V_{REF1} = 3.0V$ )

CHARACTERISTIC	SYMBOL	TEST CIR- CUIT	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Input Level	V <sub>IN</sub>	1	0~140IRE		_	1.5	1.6	V <sub>p-p</sub>
Low Frequency Gain	GV	1	S2 = 2, S3 = 2, S4 = 1 V <sub>IN</sub> = 15.734kHz, 1.5 Vdc = 2.5V		- 0.5	0.0	0.5	dB
Eroquangu Basnansa	MTF1	1	S2 = 2, S3 = 2, S4 = 1, S5 = 2	f2/f1	- 2.0	- 1.2	- 0.5	dB
Frequency Response	MTF2	1	V <sub>IN</sub> = 1.5V <sub>p-p</sub> Vdc = 2.5V	f4/f1	- 3.0	- 2.0	- 1.5	αв
Comb Characteristics	Comb	1	S2 = 2, $S3 = 2$ , S4 = 1, $S5 = 2V_{IN} = 1.5V_{p-p}Vdc = 2.5V$	f2/f3	40	45	_	dB
Linearity (Fig. 4)	L <sub>S</sub>	1	S2 = 1, S3 = 1, S4 = 1, S5 = 2	Y1/Y2	35	40	43	0/
Linearity (Fig.1)	L <sub>y</sub>	1	$V_{IN} = 5$ step signal, 1.5 $V_{p-p}$ (Fig.2)	S/Y2	57	60	63	%
Output Impedance	z <sub>o</sub>	1	S2 = 1, S3 = 1, S5 = 2 $V_{IN}$ = 15.734kHz, 1.5 Vdc = 2.5V $Z_{O}$ = $\frac{V1 - V2}{V2}$ × 40 V1 : S4 = 1, V2 : 5	5V <sub>p-p</sub>	250	400	700	Ω
Clock Leakage (4f <sub>sC</sub> Components)	L <sub>ck</sub>	1	S2 = 2, S3 = 2, S4 = 1 V <sub>IN</sub> = No input		_	5.0	20	mV <sub>rms</sub>
Fundamental Clock Leakage (f <sub>SC</sub> Components)	L <sub>sc</sub>	1	S2 = 2, S3 = 2, S4 = 1 V <sub>IN</sub> = No input	, S5 = 1	_	1.0	2.0	mV <sub>rms</sub>

C output (Ta = 25°C,  $V_{DD}$  = 5V, Clock frequency 3.579545MHz, 0.5 $V_{p-p}$ , S1 = 1, VREF1 = 3.0V)

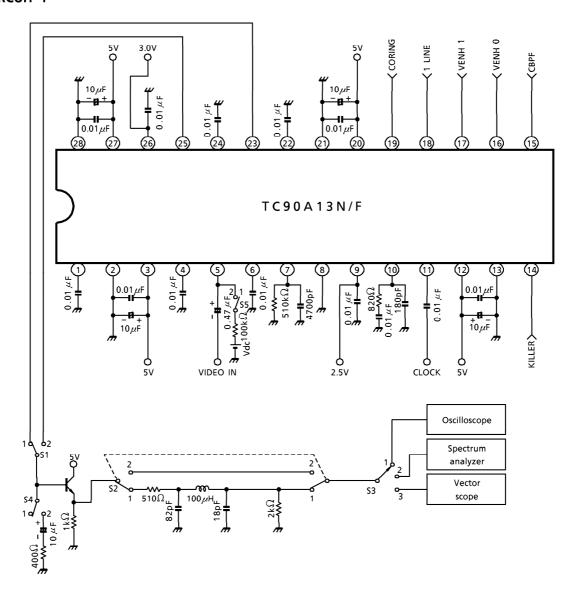
CHARACTERISTIC		SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
BPF Characteristics	WIDE	BWCW	1	S2 = 2, $S3 = 2$ , $S4 = 1$ , $S5 = 2Difference of amplitudebetween 1f_{SC} and 1f_{SC} - 503496HzV_{IN} = 1.5V_{p-p}, Vdc = 2.5V$	-0.5	-0.2		dB
	NARROW	BWCN	1	S2 = 2, $S3 = 2$ , $S4 = 1$ , $S5 = 2Difference of amplitudebetween 1f_{SC} and 1f_{SC} - 503496HzV_{IN} = 1.5V_{p-p}, Vdc = 2.5V$	- 1.0	- 0.5	_	uв
Gain		CV	1	S2 = 2, $S3 = 2$ , $S4 = 1$ , $S5 = 1V_{IN} = f_{SC}, 430 \text{mV}_{p-p}$	- 2.0	- 0.9	- 0.6	dB
Comb Characteristics		Comb	1	S2 = 2, $S3 = 2$ , S4 = 1, $S5 = 2V_{IN} = 430 \text{mV}_{p-p},Vdc = 2.5 V$	30	35	_	dB
Differential Gain		DG	1	S2 = 2, $S3 = 3$ , $S4 = 1$ , $S5 = 1V_{IN} = 5 step signal,Y = 140IRE = 1.5V_{p-p}$	0	2	5	%
Differential Phase		DP	1	C = 40IRE (Fig.2) DG = (Comax – Comin) / Comax (Fig.3)	0	2	5	o
Output Impedance		Z <sub>O</sub>	1	S2 = 2, S3 = 2, S5 = 2 $V_{IN}$ = 15.734kHz, 1.5 $V_{p-p}$ $V_{dc}$ = 2.5 $V_{dc}$ $V_{dc}$ = $\frac{V_{1} - V_{2}}{V_{2}}$ × 400 $V_{1}$ : S4 = 1, $V_{2}$ : S4 = 2	250	400	700	Ω
Clock Leak (4f <sub>sc</sub> Components)		L <sub>ck</sub>	1	S2 = 2, S3 = 2, S4 = 1, S5 = 1 V <sub>IN</sub> = No input	-	5.0	20	mV <sub>rms</sub>
Fundamental Cloc (f <sub>sc</sub> Components)		L <sub>sc</sub>	1	S2 = 2, $S3 = 2$ , $S4 = 1$ , $S5 = 1V_{IN} = No input$	_	0.3	1.0	mV <sub>rms</sub>

f1 = 15.734kHz, f2 = 3.587412MHz, f3 = 3.595279MHz, f4 = 4.783216MHz

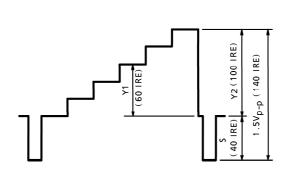
# PLL CIRCUIT CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Pull-in Frequency Range	fck	1	_	3.57	3.58	3.59	MHz
Input Amplitude (f <sub>sc</sub> Components)	Vck	1	_	0.4	0.5	_	V <sub>p-p</sub>

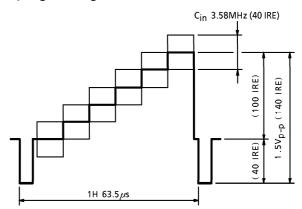
# **TEST CIRCUIT 1**



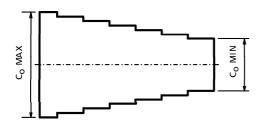
Linearity test (Fig.1)



5 Step signal (Fig.2)

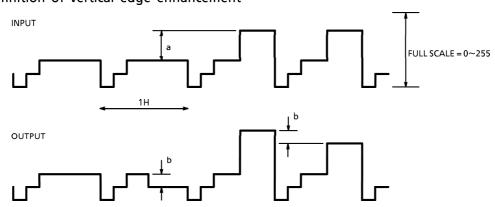


Chroma differential gain (Fig.3)



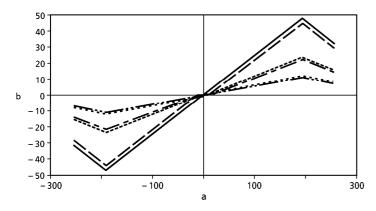
# **REFERENCE DATA**

(Fig.4-a) Definition of vertical edge enhancement

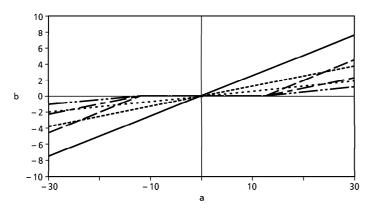


(Note) The output signal, to which the vertical edge enhancement component is added, is limited to pedestal level by the pedestal clip circuit.

(Fig.4-b) Vertical edge enhancement characteristic



(Fig.4-c) Vertical edge enhancement characteristic (detail)



The relation between a and b. (refer to Fig.4-a)

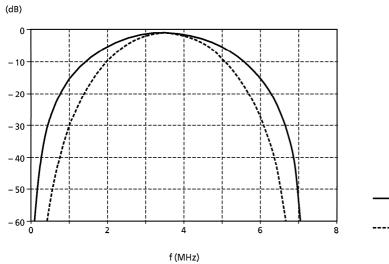
- a: The difference in luminance level is in the enhanced part of the edge.
- b: The component of vertical edge enhancement that is added to the luminance signal.

Both are expressed as digital values.

- (A) Enhance Value HIGH ----- (B) MID ---- (C) LOW
- − − (D) Enhance value HIGH −− − (E) MID −−− ⋅ (F) LOW

A, B, C : Coring = OFF D, E, F : Coring = ON

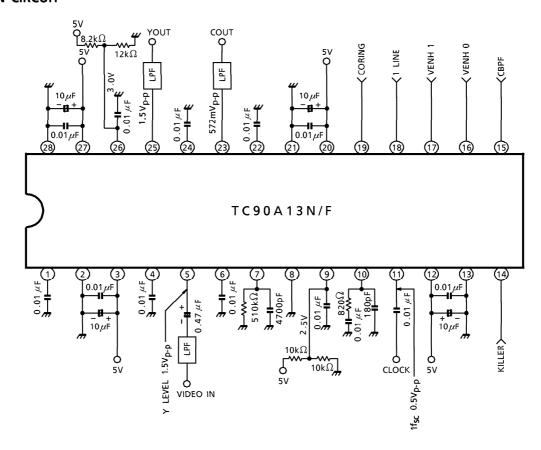
(Fig.5) Frequency characteristics of chroma output



- Wide band width

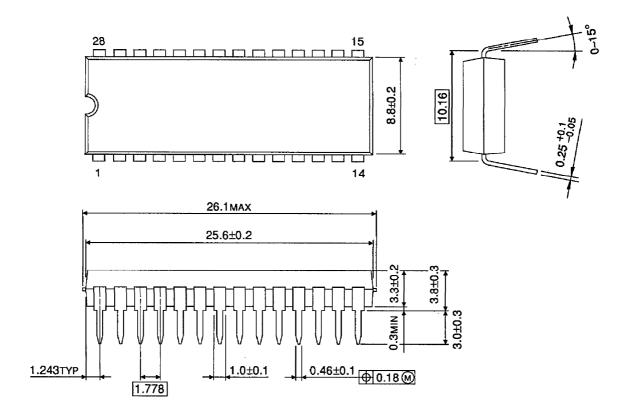
---- Narrow band width

# **APPLICATION CIRCUIT**



# **PACKAGE DIMENSIONS**

SDIP28-P-400-1.78 Unit: mm

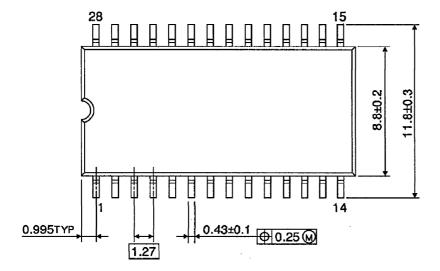


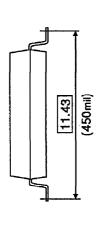
Weight: 1.7g (Typ.)

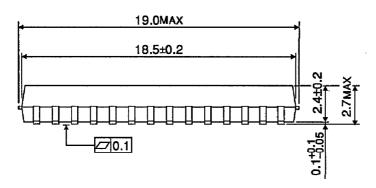
Unit: mm

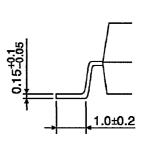
# **PACKAGE DIMENSIONS**

SOP28-P-450-1.27









Weight: 0.8g (Typ.)

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000707EBA

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